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Jason T. Dong ; Hadass S. Inbar ; Mihir Pendharkar ; Teun A. J. van Schijndel ; Elliot C. Young; Connor P. Dempsey ; Christopher J. Palmström  



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Jason T. Dong,¹ Hadass S. Inbar,¹ Mihir Pendharkar,^{2,a)} Teun A. J. van Schijndel,² Elliot C. Young,¹ Connor P. Dempsey,² and Christopher J. Palmstrøm^{1,2,b)}

AFFILIATIONS

¹Materials Department, University of California, Santa Barbara 93106, California

²Department of Electrical and Computer Engineering, University of California, Santa Barbara 93106, California

^{a)}Present address: Department of Materials Science and Engineering, Stanford University, Stanford 94305, CA

^{b)}Author to whom correspondence should be addressed: cjpalm@ucsb.edu

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The original article¹ contained errors in the reference section. Corrections have been made to the following references:

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^{a)}Present address: Department of Materials Science and Engineering, Stanford University, Stanford 94305, CA

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